

Microwave, RF & Tuner Transistors

MOS Field Effect Transistors

For complete package outlines, refer to pages PO-1 through PO-6

Type	Maximum Ratings			Characteristics ($T_A=25^\circ\text{C}$)						Case		
	V_{DS} V	I_{DS} mA	P_t mW	G_{ps} dB	NF dB	at V_{DS} V	I_D mA	f MHz	g_{fs} mS	Style	Lead Code	Leaded Equiv.
(Tetrode)												
BF930	.12	40	200	29	0.60	8	15	200	42	SOT143	1	-
BF993	20	50	200	25	1.50	15	10	200	25	SOT143	1	BF963
BF994S	20	30	200	25	1.00	15	10	200	18	SOT143	1	BF964S
BF995	20	30	200	23	1.10	15	10	200	17	SOT143	1	BF961
BF996S	20	30	200	18	1.80	15	10	800	18	SOT143	1	BF966S
BF997	20	30	200	25	1.00	15	10	200	18	SOT143	1	BF965
BF998	12	30	200	20	1.00	8	10	800	24	SOT143	1	BF988
BF1005	5	10	200	-	1.00	5	10	800	22	SOT143	1	-
BF1012	12	10	200	20	1.00	12	10	800	24	SOT143	1	-
(Triode)												
BF543	20	30	200	22	1.00	10	4	200	12	SOT23	2	BF544
BF999	20	30	200	25	1.00	10	10	200	16	SOT23	2	BF987

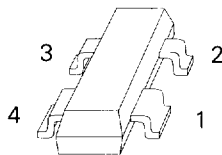
GaAsFETs

Type	Maximum Ratings				Characteristics ($T_A=25^\circ\text{C}$)						Case		
	V_{DS} V	V_{GS} V	I_{DS} mA	P_{tot} mW	g_m mS	F dB	G_a dB	f GHz	MAG dB	P_{-1dB} dBm	Style	Lead Code	Leaded Equiv.
CFY30	5	-4...+0.5	80	250	30	1.40	11.50	4.0	-	16.0	SOT143	3	-
CFY35-20	5	-4...+0.0	60	180	25	≤ 2.00	≥ 8.00	12.0	-	-	MW4	3	CFY 25-20
CFY35-23	5	-4...+0.0	60	180	25	≤ 2.30	≥ 8.00	12.0	-	-	MW4	3	CFY 25-23
CLY2	8	-6...+0.0	600	900			15.00	1.8	-	22.5	MW6	69	-
CLY5	8	-6...+0.0	1200	2000			9.50	1.8	-	26.5	SOT223	70	-
CLY10	8	-6...+0.0	2100	2000			9.50	1.8	-	32.0	SOT223	70	-

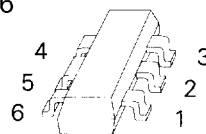
Dual-Gate GaAsFET

Type	Maximum Ratings				Characteristics ($T_A=25^\circ\text{C}$)				Case		
	V_{DS} V	V_{G1S} V	V_{G2S} V	I_D mA	I_{DSS} mA	F dB	G_{ps} dB	f GHz	Style	Lead Code	Leaded Equiv.
CF739	10	-6	-6	80	10	1.80	17	1.75	SOT143	4	-
CF750	8	-5	-	80	2	1.90	10	1.80	SOT143	5	-

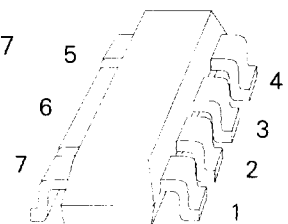
MW-4



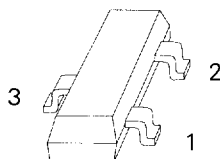
MW-6



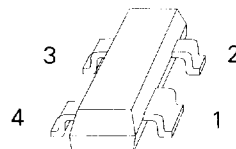
MW-7



SOT-23



SOT-143



SOT-223

